
2SC5139

Silicon NPN Epitaxial

HITACHI

ADE-208-226
1st. Edition

Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 11 \text{ GHz typ}$
- High gain, low noise figure
 $PG = 15 \text{ dB typ, NF} = 1.1 \text{ dB typ at } f = 900 \text{ MHz}$

Outline

SMPAK



1. Emitter
2. Base
3. Collector

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_{C}	50	mA
Collector power dissipation	P_{C}	80	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note: Marking is "YZ-".

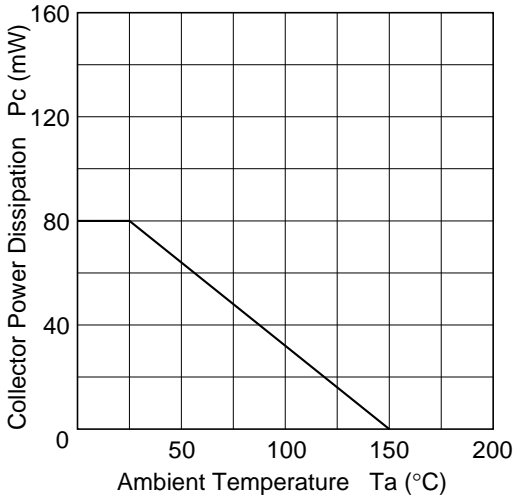
Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

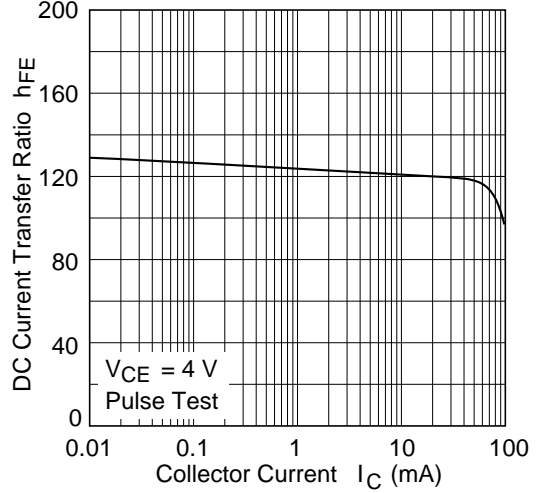
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	15	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{\text{CB}} = 12 \text{ V}$, $I_{\text{E}} = 0$
	I_{CEO}	—	—	1	mA	$V_{\text{CE}} = 8 \text{ V}$, $R_{\text{BE}} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{\text{EB}} = 1.5 \text{ V}$, $I_{\text{C}} = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$
Collector output capacitance	C_{ob}	—	0.65	1.15	pF	$V_{\text{CB}} = 5 \text{ V}$, $I_{\text{E}} = 0$, $f = 1 \text{ MHz}$
Gain bandwidth product	f_{T}	8	11	—	GHz	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$
Power gain	PG	11.5	15	—	dB	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$, $f = 900 \text{ MHz}$
Noise figure	NF	—	1.1	2.0	dB	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 5 \text{ mA}$, $f = 900 \text{ MHz}$

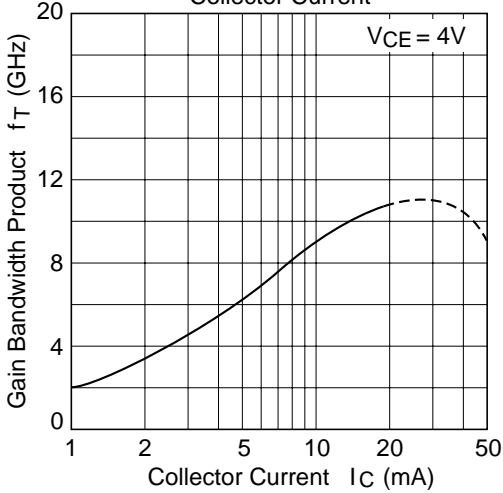
Maximum Collector Dissipation Curve



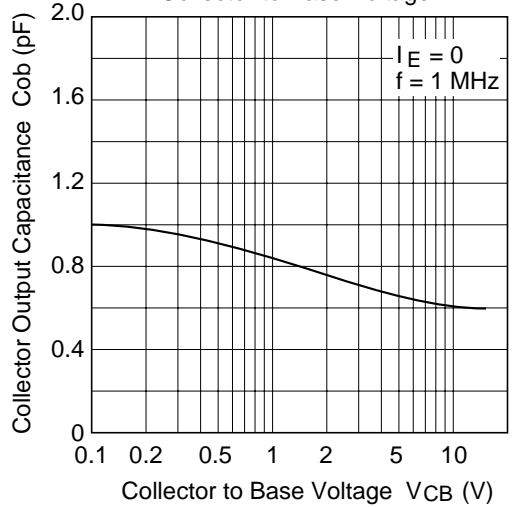
DC Current Transfer Ratio vs. Collector Current

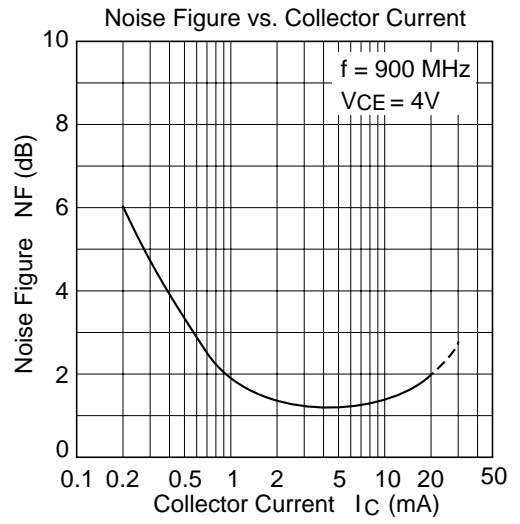
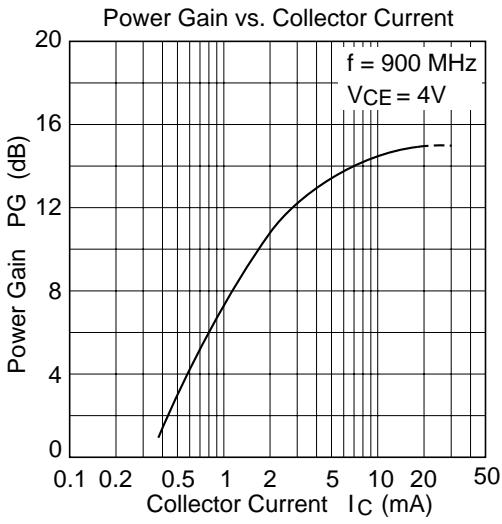


Gain Bandwidth Product vs. Collector Current

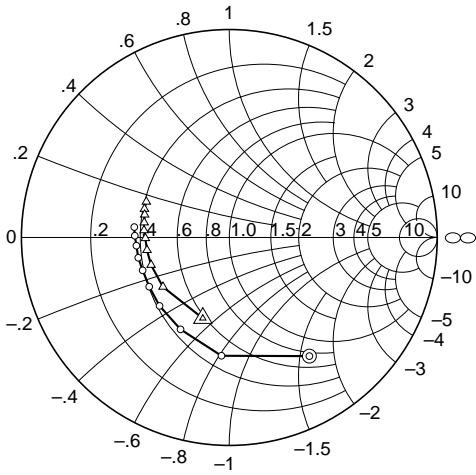


Collector Output Capacitance vs. Collector to Base Voltage



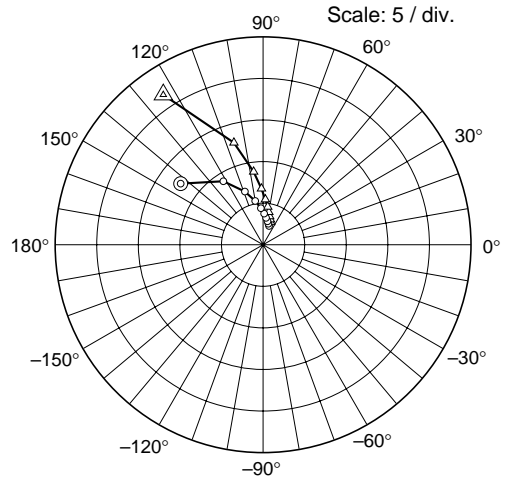


S11 Parameter vs. Frequency



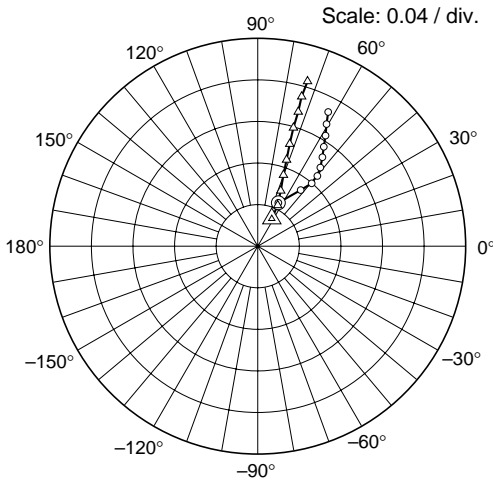
Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (IC = 5 mA)
 △ (IC = 20 mA)

S21 Parameter vs. Frequency



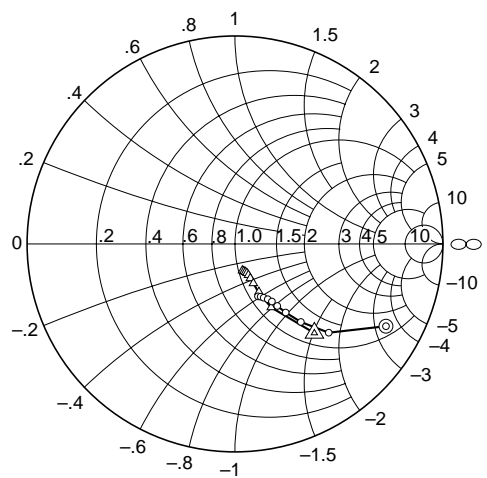
Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (IC = 5 mA)
 △ (IC = 20 mA)

S12 Parameter vs. Frequency



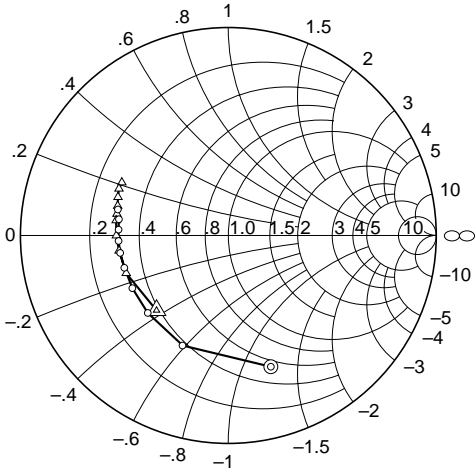
Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (IC = 5 mA)
 △ (IC = 20 mA)

S22 Parameter vs. Frequency



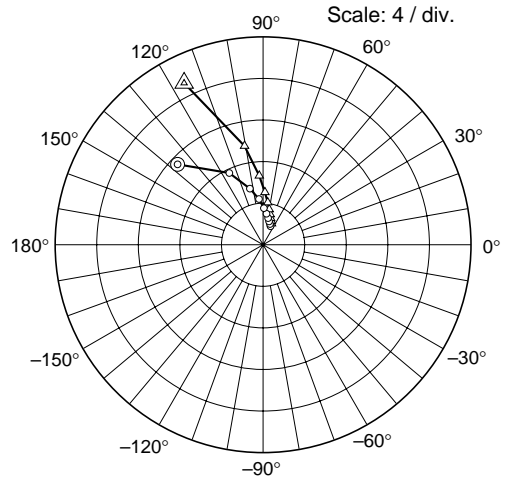
Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (IC = 5 mA)
 △ (IC = 20 mA)

S11 Parameter vs. Frequency



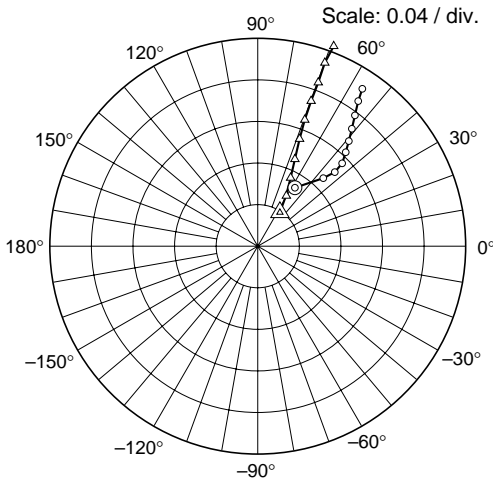
Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (I_C = 5 mA)
 △ (I_C = 20 mA)

S21 Parameter vs. Frequency



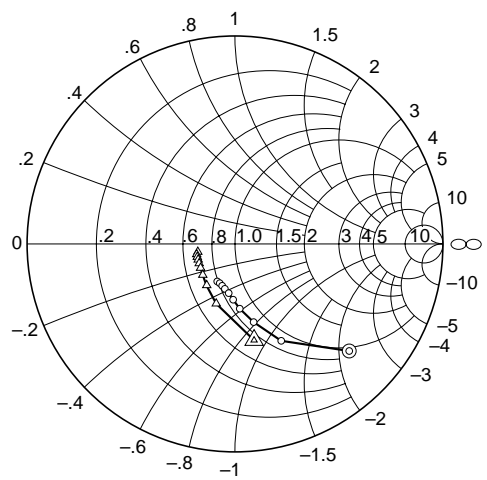
Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (I_C = 5 mA)
 △ (I_C = 20 mA)

S12 Parameter vs. Frequency



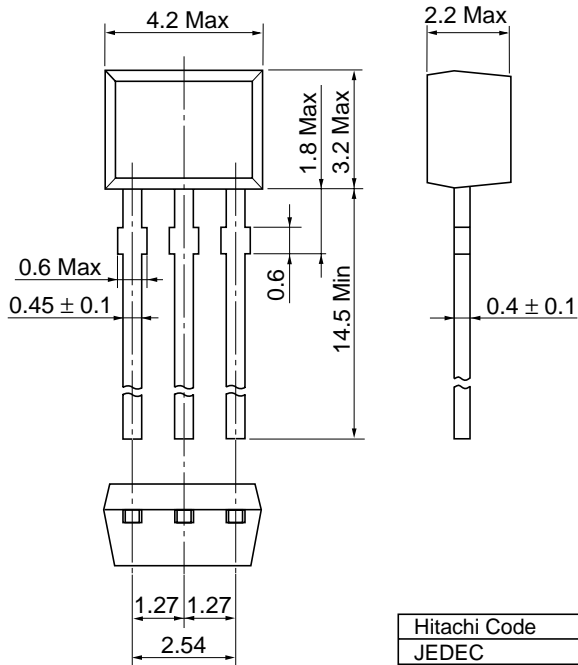
Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (I_C = 5 mA)
 △ (I_C = 20 mA)

S22 Parameter vs. Frequency



Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ (I_C = 5 mA)
 △ (I_C = 20 mA)

Unit: mm



Hitachi Code	SPAK
JEDEC	—
EIAJ	—
Weight (reference value)	0.10 g

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